

isc Silicon NPN Power Transistor

BU999

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)}=140V(\text{Min})$
- High Switching Speed
- High Power Dissipation

APPLICATIONS

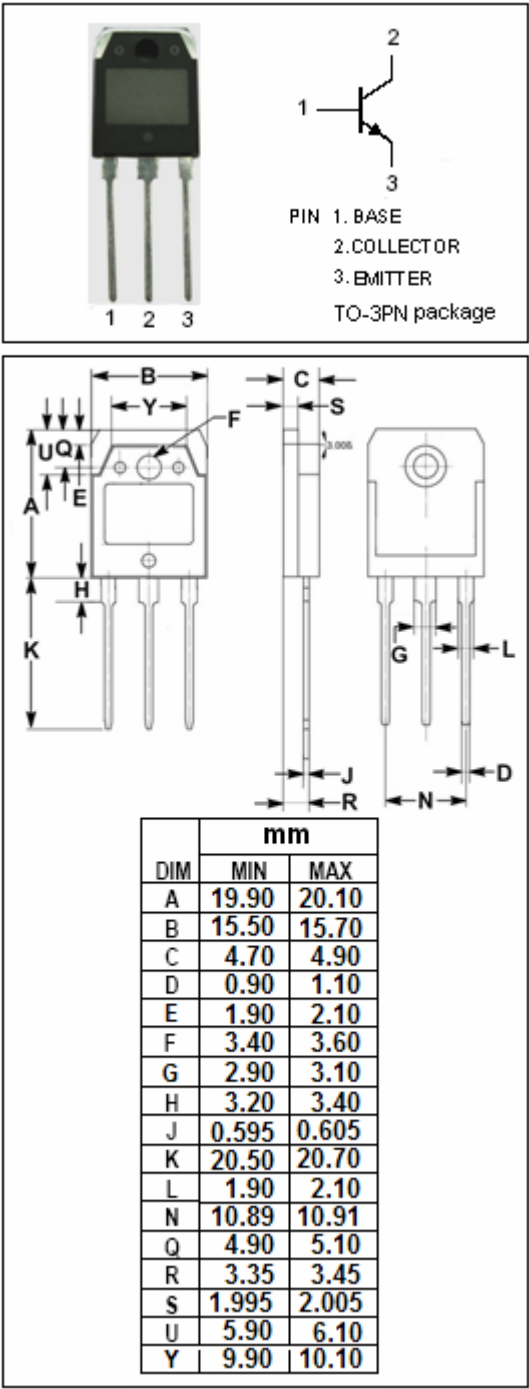
- Designed for switching and linear applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	160	V
V_{CEO}	Collector-Emitter Voltage	140	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	25	A
I_{CP}	Collector Current-Pulse	40	A
I_B	Base Current-Continuous	10	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}\text{C}$	106	W
T_J	Junction Temperature	200	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-55~200	$^{\circ}\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance,Junction to Case	2.08	$^{\circ}\text{C/W}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=50\text{mA}; I_B=0$	140			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C=10\text{A}; I_B=1\text{A}$			0.8	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C=25\text{A}; I_B=2.5\text{A}$			1.5	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	$I_C=10\text{A}; I_B=1\text{A}$			1.8	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	$I_C=25\text{A}; I_B=2.5\text{A}$			2.5	V
$V_{BE(on)}$	Base -Emitter On Voltage	$I_C=10\text{A}; V_{CE}=2\text{V}$			1.8	V
I_{CEX}	Collector Cutoff Current	$V_{CE}=140\text{V}; V_{BE}=-1.5\text{V}$			10	μA
I_{CBO}	Collector Cutoff Current	$V_{CB}=160\text{V}; I_E=0$			100	μA
I_{CEO}	Collector Cutoff Current	$V_{CE}=70\text{V}; I_B=0$			50	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=6\text{V}; I_C=0$			100	μA
h_{FE-1}	DC Current Gain	$I_C=0.5\text{A}; V_{CE}=2\text{V}$	35			
h_{FE-2}	DC Current Gain	$I_C=10\text{A}; V_{CE}=2\text{V}$	25		100	
h_{FE-3}	DC Current Gain	$I_C=25\text{A}; V_{CE}=2\text{V}$	12			

Switching times

t_{on}	Turn-on Time	$I_C=10\text{A}, I_{B1}=-I_{B2}=1\text{A}, V_{CC}=80\text{V}$			0.3	μs
t_{stg}	Storage Time				1.5	μs
t_f	Fall Time				0.25	μs